

EAST - [-1.wsp:1]

File View Edit Tools Window Help

☐ Drafts
 BRS: macro and dram
☐ Pending
☐ Active
 L3: (431) bit and w
 L4: (3) 3 and redun
☐ Failed
☐ Saved

DBs: USPAT, US-PGPHUB, EPO, JPD, DERWENT, IBM, TDB ☐ Plural

Default operator: OR ☒ Highlight all hit terms initially

3 and redundant adj word adj line

| | U | I | Document ID | Issue Date | Pages | Title | Current OR | Current XRef | Ret |
|---|--------------------------|--------------------------|--------------|------------|-------|---|------------|-------------------------|-----|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 5618742 A | 19970408 | 28 | Method of making flash EPROM with conductive sidewall | 438/263 | 438/264; 438/267 | |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 5526307 A | 19960611 | 32 | Flash EPROM integrated circuit architecture | 365/185.01 | 257/316; 365/185.09; | |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | EP 1102168 A | 20010523 | 8 | Integrated memory with memory cells and reference | | | |

Ready NUM

 Saved

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8 and replac$
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☒ Highlight all hit terms inline

 ABS form
 IS&R form
 Image
 Text

| | U | I | Document ID | Issue Date | Pages | Title | Current OR | Current XRef |
|----|-------------------------------------|--------------------------|----------------------|------------|-------|---|------------|----------------------------|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 6295231 B1 | 20010925 | 27 | High-speed cycle clock-synchronous memory | 365/189.01 | 365/230.03 ; 365/230.08 |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 6292383 B1 | 20010918 | 11 | Redundant memory cell for dynamic random access | 365/69 | 365/200 ; 365/63 |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | <u>US 6243306 B1</u> | 20010605 | 15 | Defect management engine for generating a unified address | 365/200 | 365/189.07 |
| 4 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 6141267 A | 20001031 | 28 | Defect management engine for semiconductor memories and | 365/200 | 365/185.09 ; 365/51 |
| 5 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | <u>US 5963489 A</u> | 19991005 | 20 | Method and apparatus for redundancy word line | 365/200 | 365/149 ; 714/711 |
| 6 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5828602 A | 19981027 | 56 | Memory system having multiple programmable | 365/185.2 | 365/185.21 |
| 7 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | <u>US 5796653 A</u> | 19980818 | 12 | Circuit for the selection of redundant memory elements | 365/185.09 | 365/185.12 ; 365/200 |
| 8 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5754483 A | 19980519 | 11 | Reference word line and data propagation reproduction | 365/194 | 365/210 |
| 9 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5602044 A | 19970211 | 6 | Memory with on-chip detection of bit line leaks | 438/4 | 438/15 ; 438/6 |
| 10 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5555212 A | 19960910 | 23 | Method and apparatus for redundancy word line | 365/200 | 365/149 ; 365/201 |
| 11 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5539694 A | 19960723 | 6 | Memory with on-chip detection of bit line leaks | 365/189.09 | 365/189.07 ; 365/201 |

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File View Edit Tools Window Help

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Searching:
 DBs: USPAT, US-PGPUB, EPD, JPD, DERWENT, IBM TDB
 Default operator: DR
☐ Plural ☐ Synonyms
☒ Highlight all hit terms initially

word-lines or word adj lines) and memory and reference adj cell\$) and redundan\$) and activ\$ same connected) and replac\$)

| | U | I | Document ID | Issue Date | Pages | Title | Current OR | Current XRef |
|----|-------------------------------------|--------------------------|---------------|------------|-------|---|------------|----------------------------|
| 10 | <input type="checkbox"/> | <input type="checkbox"/> | US 5453391 A | 19950926 | 16 | Method for manufacturing a contactless floating gate | 438/263 | 438/261 |
| 11 | <input type="checkbox"/> | <input type="checkbox"/> | US 5450361 A | 19950912 | 81 | Semiconductor memory device having redundant memory | 365/200 | 365/189.07 ; 365/203 |
| 12 | <input type="checkbox"/> | <input type="checkbox"/> | US 5399928 A | 19950321 | 13 | Negative voltage generator for flash EPROM design | 327/434 | 326/92 ; 327/536 |
| 13 | <input type="checkbox"/> | <input type="checkbox"/> | US 5399891 A | 19950321 | 20 | Floating gate or flash EPROM transistor array having | 365/185.16 | 257/314 ; 257/315 |
| 14 | <input type="checkbox"/> | <input type="checkbox"/> | US 5327383 A | 19940705 | 43 | Method and circuitry for erasing a nonvolatile | 365/185.24 | 365/185.09 ; 365/185.12 |
| 15 | <input type="checkbox"/> | <input type="checkbox"/> | US 5031151 A | 19910709 | 14 | Wordline drive inhibit circuit implementing | 365/195 | 365/200 ; 365/210 |
| 16 | <input type="checkbox"/> | <input type="checkbox"/> | US 5023839 A | 19910611 | 6 | Redundant semiconductor memory device | 365/185.21 | 365/185.09 |
| 17 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5022006 A | 19910604 | 14 | Semiconductor memory having bit lines with isolation | 365/200 | 365/51 ; 714/711 |
| 18 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | EP 1102168 A2 | 20011029 | | Integrated memory with memory cells and reference | | |
| 19 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5022006 A | 19910604 | 14 | Semiconductor memory using redundant words for repair - | | |

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File View [db] Tools Window Help

☐ L2: (1333759) 1 and
☐ L3: (851) 2 and ref
☐ L4: (86) 3 and redu
☐ L5: (54) 4 and redu
☐ L6: (33) 5 and acti
☐ L7: (27) 6 and sens
☐ Failed
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Search In:
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☐ Plural ☐ Synonyms
☒ Highlight all hit terms initially
 6 and sense

☒ BRS term ☒ I&R term ☐ Image ☐ Text

| | U | 1 | Document ID | Issue Date | Pages | Title | Current OR | Current XRef |
|----|-------------------------------------|--------------------------|---------------------|------------|-------|---|------------|----------------------------|
| 18 | <input type="checkbox"/> | <input type="checkbox"/> | US 5453391 A | 19950926 | 16 | Method for manufacturing a contactless floating gate | 438/263 | 438/261 |
| 19 | <input type="checkbox"/> | <input type="checkbox"/> | US 5399891 A | 19950321 | 20 | Floating gate or flash EPROM transistor array having | 365/185.16 | 257/314 ; 257/315 |
| 20 | <input type="checkbox"/> | <input type="checkbox"/> | US 5377147 A | 19941227 | 42 | Method and circuitry for preconditioning shorted rows | 365/185.09 | 365/185.12 ; 365/185.21 |
| 21 | <input type="checkbox"/> | <input type="checkbox"/> | US 5347489 A | 19940913 | 41 | Method and circuitry for preconditioning shorted rows | 365/203 | 365/185.2 ; 365/185.24 |
| 22 | <input type="checkbox"/> | <input type="checkbox"/> | US 5327383 A | 19940705 | 43 | Method and circuitry for erasing a nonvolatile | 365/185.24 | 365/185.09 ; 365/185.12 |
| 23 | <input type="checkbox"/> | <input type="checkbox"/> | US 5237535 A | 19930817 | 17 | Method of repairing overerased cells in a flash | 365/185.3 | 365/185.12 ; 365/185.19 |
| 24 | <input type="checkbox"/> | <input type="checkbox"/> | US 5142496 A | 19920825 | 16 | Method for measuring V.sub.T's less than zero without | 365/201 | 365/104 ; 365/185.09 |
| 25 | <input type="checkbox"/> | <input type="checkbox"/> | US <u>5031151</u> A | 19910709 | 14 | Wordline drive inhibit circuit implementing | 365/195 | 365/200 ; 365/210 |
| 26 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US <u>5022006</u> A | 19910604 | 14 | Semiconductor memory having bit lines with isolation | 365/200 | 365/51 ; 714/711 |
| 27 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 4874500 A | 19891017 | 18 | Microelectrochemical sensor and sensor array | 204/412 | 204/408 ; 204/416 |

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 Default operator: DR
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| | U | 1 | Document ID | Issue Date | Pages | Title | Current OR | Current XRef |
|----|--------------------------|--------------------------|---------------|------------|-------|--|------------|----------------------------|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 6292383 B1 | 20010918 | 11 | Redundant memory cell for dynamic random access | 365/69 | 365/200 ; 365/63 |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 6282145 B1 | 20010828 | 74 | Array architecture and operating methods for | 365/230.06 | 365/51 ; 365/63 |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | US 6275434 B1 | 20010814 | 39 | Semiconductor memory | 365/206 | 365/208 ; 365/63 |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | US 6212096 B1 | 20010403 | 10 | Data reading path management architecture for a memory | 365/185.02 | 365/185.17 |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US 6091655 A | 20000718 | 39 | Semiconductor memory | 365/210 | 365/149 ; 365/189.12 |
| 6 | <input type="checkbox"/> | <input type="checkbox"/> | US 6085233 A | 20000704 | 86 | System and method for cellular network computing | 709/216 | 709/212 ; 709/237 |
| 7 | <input type="checkbox"/> | <input type="checkbox"/> | US 5961653 A | 19991005 | 18 | Processor based BIST for an embedded memory | 714/7 | 714/30 ; 714/718 |
| 8 | <input type="checkbox"/> | <input type="checkbox"/> | US 5953255 A | 19990914 | 35 | Low voltage, low current hot-hole injection erase and | 365/185.29 | 365/185.28 ; 365/185.3 |
| 9 | <input type="checkbox"/> | <input type="checkbox"/> | US 5946237 A | 19990831 | 13 | Nonvolatile memory device capable of reading data with | 365/185.2 | 365/185.09 ; 365/185.11 |
| 10 | <input type="checkbox"/> | <input type="checkbox"/> | US 5854004 A | 19981229 | 86 | Process for screening substances capable of | 435/7.21 | 435/6 ; 435/8 |
| 11 | <input type="checkbox"/> | <input type="checkbox"/> | US 5691938 A | 19971125 | 18 | Non-volatile memory cell and array architecture | 365/185.11 | 257/316 ; 365/185.06 |

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|----|--------------------------|--------------------------|--------------|------------|-------|---|------------|----------------------------|
| 12 | <input type="checkbox"/> | <input type="checkbox"/> | US 5633185 A | 19970527 | 17 | Method of making a non-volatile memory cell | 438/258 | 438/279 |
| 13 | <input type="checkbox"/> | <input type="checkbox"/> | US 5618742 A | 19970408 | 28 | Method of making flash EPROM with conductive sidewall | 438/263 | 438/264 ; 438/267 |
| 14 | <input type="checkbox"/> | <input type="checkbox"/> | US 5610867 A | 19970311 | 14 | DRAM signal margin test method | 365/201 | 365/189.05 ; 365/189.07 |
| 15 | <input type="checkbox"/> | <input type="checkbox"/> | US 5572707 A | 19961105 | 8 | Nonvolatile memory with a programmable configuration | 711/170 | 326/38 ; 711/102 |
| 16 | <input type="checkbox"/> | <input type="checkbox"/> | US 5559739 A | 19960924 | 14 | Dynamic random access memory with a simple test | 365/189.01 | 365/201 ; 365/203 |
| 17 | <input type="checkbox"/> | <input type="checkbox"/> | US 5526307 A | 19960611 | 32 | Flash EPROM integrated circuit architecture | 365/185.01 | 257/316 ; 365/185.09 |
| 18 | <input type="checkbox"/> | <input type="checkbox"/> | US 5453391 A | 19950926 | 16 | Method for manufacturing a contactless floating gate | 438/263 | 438/261 |
| 19 | <input type="checkbox"/> | <input type="checkbox"/> | US 5399891 A | 19950321 | 20 | Floating gate or flash EPROM transistor array having | 365/185.16 | 257/314 ; 257/315 |
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